

3600.3245  
June 13, 2002 (11:47AM)



RECEIVED  
JUN 19 2002  
TECHNOLOGY CENTER 1700  
Docket AM-3245

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**In re Application of:** Hoiman HUNG et al.

**Attorneys Docket:** AM-3245

**Serial No.:** 09/276,376

**Art Unit No.:** 1746

**Filed:** March 25, 1999

**Examiner:** A. Olsen

**For:** "ENHANCEMENT OF SILICON OXIDE ETCH RATE AND NITRIDE SELECTIVITY USING HEXAFLUOROBUTADIENE OR OTHER HEAVY PERFLUOROCARBON"

Commissioner of Patents and Trademarks  
Washington, DC 20231

AMENDMENT UNDER 37 CFR §1.115

Sir:

In a Preliminary Amendment for consideration before initial examination of the Continued Prosecution Application (CPA) filed in response to the Office Action of April 26, 2002, please amend the above application as follows:

**In the title:**

**Please change the title to:**

Enhancement of Silicon Oxide Etch Rate and Nitride Selectivity Using Hexafluorobutadiene or Other Heavy Perfluorocarbon

**Replace all claims with:**

1. (Already Twice Amended) A process for etching an oxide layer in the presence of a nitride layer, wherein said oxide layer is preformed with holes extending downwardly from a top surface thereof and corners of said oxide layer at tops of said holes are exposed during the

D